

五、著作目錄：

(1) 請詳列個人最近五年內（此段期間曾生產、請育嬰假或生產並請育嬰假者，得延長至七年內，但須檢附相關證明文件）發表之學術性著作，包括：期刊論文、專書及專書論文、研討會論文、技術報告及其他等，並請依各類著作之重要性自行排列先後順序。

(2) 各類著作請按發表時間先後順序填寫。各項著作請依作者姓名（按原出版之次序）、出版年、月份、題目、期刊名稱（專書出版社）、起迄頁數之順序填寫，被接受刊登尚未正式出版者請附被接受函。(3) 若期刊屬於SCI、EI、SSCI或A&HCI等時，請註明；若著作係經由國科會補助之研究計畫所產生，請於最後填入相關之國科會計畫編號。

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